L Number	Hits	Search Text	DB	Time stamp
1	2	(MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") with ("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off")	USPAT; US-PGPUB	2004/06/23 10:40
2	79	(MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") and ("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off")	USPAT; US-PGPUB	2004/06/23 10:36
4	0	((MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") and (("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") with ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling"))) not (((MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") and ("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off")) not ((MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") same ("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off")))	USPAT; US-PGPUB	2004/06/23 10:37

3	4	(MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") same ("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off")	USPAT; US-PGPUB	2004/06/23 10:37
5	75	((MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") and ("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off")) not ((MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") same ("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off"))	USPAT; US-PGPUB	2004/06/23 10:37
6	35	(MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") and (("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") same ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling"))	USPAT; US-PGPUB	2004/06/23 10:37

7	0	((MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") and (("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") same ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling"))) not ((MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") and ("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off"))	USPAT; US-PGPUB	2004/06/23 10:37
9	201	("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") with ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling")	USPAT; US-PGPUB	2004/06/23 10:37
10	79264	438/$7.ccls.	USPAT; US-PGPUB	2004/06/23 10:37
8	13	(MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") and (("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") with ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling"))	USPAT; US-PGPUB	2004/06/23 10:37
12	41573	magneto or magnetoresistive or "magneto-resistive"	USPAT; US-PGPUB	2004/06/23 10:41
13	11	((("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") with ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling")) and 438/$7.ccls.) and "25"	USPAT; US-PGPUB	2004/06/23 10:39
14	0	((("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") with ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling")) and 438/$7.ccls.) and (magneto or magnetoresistive or "magneto-resistive")	USPAT; US-PGPUB	2004/06/23 10:38
15	3895171	@ad<20030320	USPAT; US-PGPUB	2004/06/23 10:42

11	22	((MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") and (("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") same ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling"))) not ((MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory") and (("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") with ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling")))	USPAT; US-PGPUB	2004/06/23 10:38
16	26	((("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") with ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling")) and 438/$7.ccls.) and @ad<20030320	USPAT; US-PGPUB	2004/06/23 10:38
17	26	(("lift off" or "lift-off" or "lifts off" or "lifts-off" or "lifted off" or "lifted-off" or "lifting off" or "lifting-off") with ("ion milling" or "ion-milling" or "ion beam milling" or "ion-beam-milling")) and 438/$7.ccls.	USPAT; US-PGPUB	2004/06/23 10:39
18	262	((438/670) or (438/951)).CCLS.	USPAT; US-PGPUB	2004/06/23 10:40
19	1959	MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory"	USPAT; US-PGPUB	2004/06/23 10:40
20	0	(((438/670) or (438/951)).CCLS.) and (MRAM or MRAMs or "MRAM's" or "magnetoresistive random access memory" or "magneto resistive random access memory" or "magneto-resistive random access memory" or "magnetoresistive-random access memory" or "magnetoresistive-random-access-memory" or "magneto-resistive-random-access-memory")	USPAT; US-PGPUB	2004/06/23 10:40
21	1	(magneto or magnetoresistive or "magneto-resistive") and (((438/670) or (438/951)).CCLS.)	USPAT; US-PGPUB	2004/06/23 10:41

22	41895	(remove or removes or removed or removing or removal) with (PR or photoresist or photoresists or "photo resist" or "photo-resist" or "photo resists" or "photo-resists")	USPAT; US-PGPUB	2004/06/23 10:44
23	142	(((438/670) or (438/951)).CCLS.) and ((remove or removes or removed or removing or removal) with (PR or photoresist or photoresists or "photo resist" or "photo-resist" or "photo resists" or "photo-resists"))	USPAT; US-PGPUB	2004/06/23 10:44